AN INTEGRATED CIRCUIT CHIP

ABSTRACT

An integrated circuit with FETs having an essentially uniform gate oxide thickness and FETs having gate oxide thickness enhanced along the sides. FETs with enhanced gate oxide (164) have an ONO layer diffused with Potassium in close proximity to the enhanced (thicker) oxide, and, as a result, have a slightly higher V_t and much more attenuated soft turn on.

Fig. 3C

This Sheet Has Been Replaced

